

PJQ4542S6VP-AU

40V N-Channel Enhancement Mode MOSFET

Voltage **40 V** **Current** **125 A**

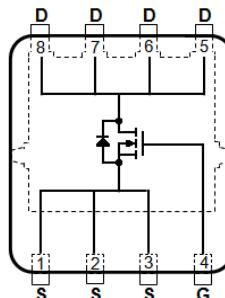
Features

- $R_{DS(ON)}$, $V_{GS} @ 10V$, $I_D @ 20A < 2.9m\Omega$
- $R_{DS(ON)}$, $V_{GS} @ 7V$, $I_D @ 10A < 4m\Omega$
- Excellent FOM
- Standard Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.03 grams

DFN3333-8L



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^(Note 3)	I_D	125	A
$T_C=100^\circ C$		89	
Pulsed Drain Current ^(Note 1)	I_{DM}	500	W
Power Dissipation	P_D	86	
$T_C=100^\circ C$		43	
Continuous Drain Current ^(Note 4)	I_D	21	A
$T_A=70^\circ C$		18	
Power Dissipation	P_D	2.5	W
$T_A=70^\circ C$		1.8	
Single Pulse Avalanche Current ^(Note 5)	I_{AS}	18	A
Single Pulse Avalanche Energy ^(Note 5)	E_{AS}	145	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~175	°C
Thermal Resistance ^(Note 4)	Junction to Case	$R_{\theta JC}$	°C/W
	Junction to Ambient	$R_{\theta JA}$	

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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\mu\text{A}$	40	-	-	V
Gate Threshold Voltage	$\text{V}_{\text{GS}(\text{th})}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=250\mu\text{A}$	2	2.8	3.5	
Drain-Source On-State Resistance	$\text{R}_{\text{DS}(\text{on})}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D=20\text{A}$	-	2.3	2.9	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=7\text{V}, \text{I}_D=10\text{A}$	-	3.1	4	
Zero Gate Voltage Drain Current	I_{DSS}	$\text{V}_{\text{DS}}=40\text{V}, \text{V}_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	$\text{V}_{\text{GS}}=\pm 20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Dynamic ^(Note 6)						
Total Gate Charge	Q_g	$\text{V}_{\text{DS}}=32\text{V}, \text{I}_D=20\text{A}, \text{V}_{\text{GS}}=10\text{V}$	-	37	50	nC
Gate-Source Charge	Q_{gs}		-	7.9	-	
Gate-Drain Charge	Q_{gd}		-	12.4	-	
Input Capacitance	C_{iss}	$\text{V}_{\text{DS}}=25\text{V}, \text{V}_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	1985	2580	pF
Output Capacitance	C_{oss}		-	738	1040	
Reverse Transfer Capacitance	Crss		-	50	88	
Gate resistance	R_g	$f=1\text{MHz}$	-	2.4	-	Ω
Turn-On Delay Time	$\text{td}_{(\text{on})}$	$\text{V}_{\text{DS}}=32\text{V}, \text{I}_D=20\text{A}, \text{V}_{\text{GS}}=10\text{V}, \text{R}_G=3\Omega$ <small>(Note 2)</small>	-	10.5	-	ns
Turn-On Rise Time	tr		-	15	-	
Turn-Off Delay Time	$\text{td}_{(\text{off})}$		-	30	-	
Turn-Off Fall Time	tf		-	18	-	
Drain-Source Diode						
Diode Forward Current	I_s	$\text{T}_{\text{C}}=25^\circ\text{C}$ (Package Limit)	-	-	94	A
Pulsed Diode Forward Current	I_{sm}		-	-	500	
Diode Forward Voltage	V_{SD}	$\text{I}_s=20\text{A}, \text{V}_{\text{GS}}=0\text{V}$	-	0.8	1.3	V
Reverse Recovery Time	Tr_{r}	$\text{V}_{\text{DD}}=32\text{V}, \text{V}_{\text{GS}}=0\text{V}, \text{I}_s=20\text{A}, \text{dI}_s/\text{dt}=100\text{A}/\text{us}$	-	30	-	ns
Reverse Recovery Charge	Q_{rr}		-	16	-	

NOTES :

1. Pulse width $\leq 100\text{us}$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature typical characteristics.
3. Chip capability with an $R_{\text{eJC}}=1.75^\circ\text{C}/\text{W}$, Package limited 100A.
4. R_{eJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
5. E_{AS} is calculated based on the condition of $L=1\text{mH}, I_{\text{AS}}=17\text{A}, V_{\text{DD}}=30\text{V}, V_{\text{GS}}=10\text{V}$. 100% test at $L=0.5\text{mH}, I_{\text{AS}}=18\text{A}$ in production.
6. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

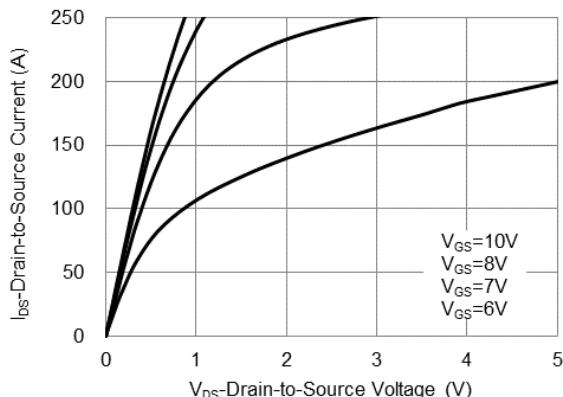


Fig.1 On-Region Characteristics

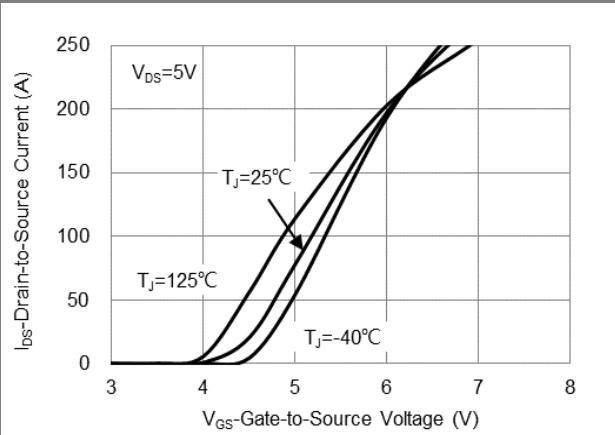


Fig.2 Transfer Characteristics

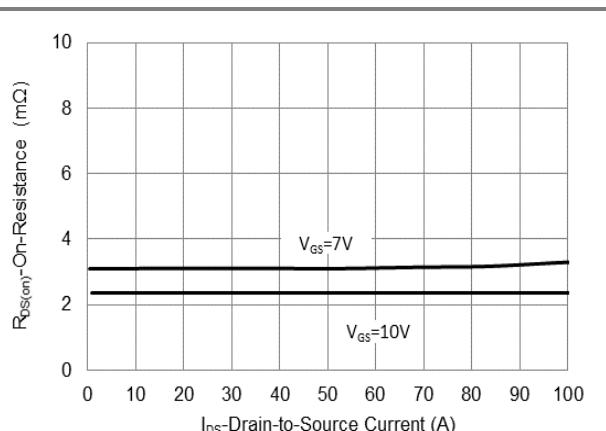


Fig.3 On-Resistance vs. Drain Current

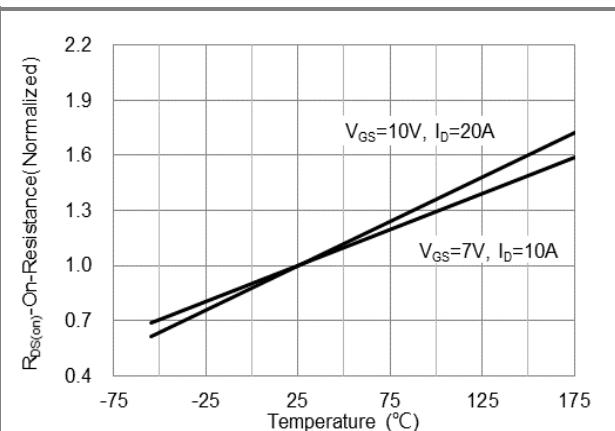


Fig.4 On-Resistance vs. Junction temperature

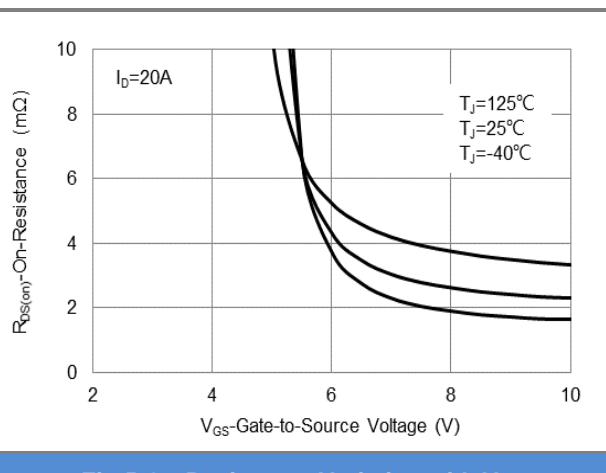


Fig.5 On-Resistance Variation with V_G

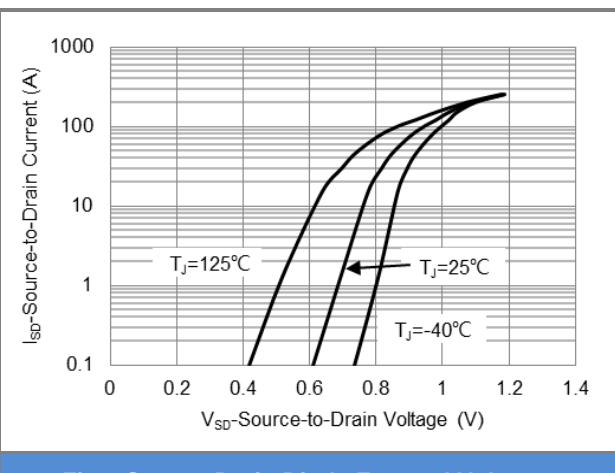


Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

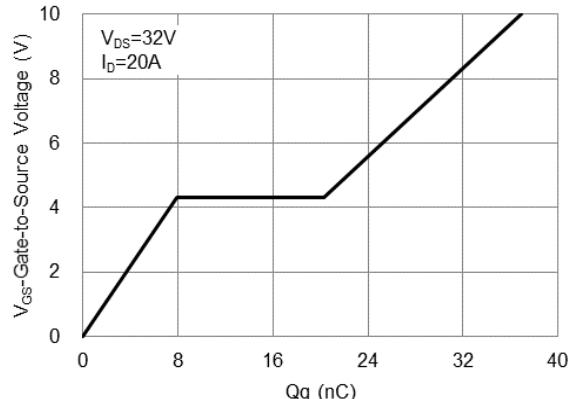


Fig.7 Gate-Charge Characteristics

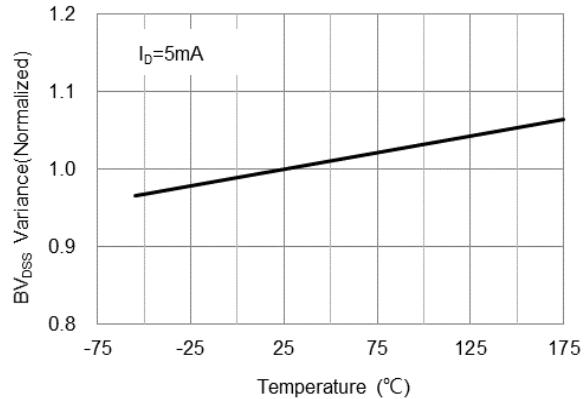


Fig.8 Breakdown Voltage Variation vs. Temperature

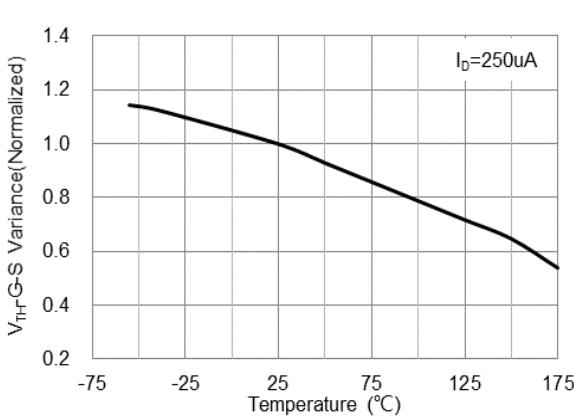


Fig.9 Threshold Voltage Variation with Temperature

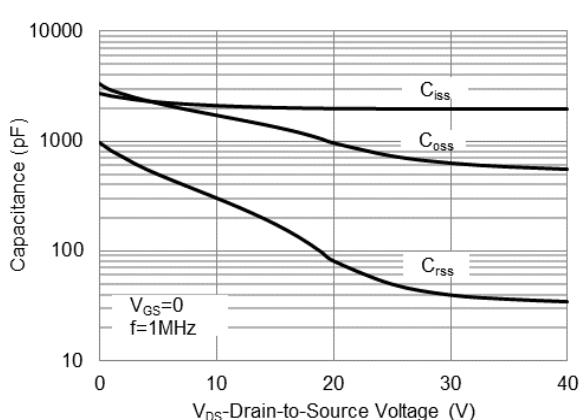


Fig.10 Capacitance vs. Drain-Source Voltage

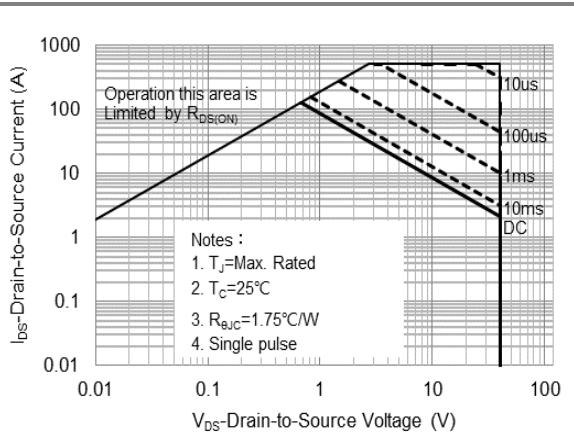


Fig.11 Maximum Safe Operating Area

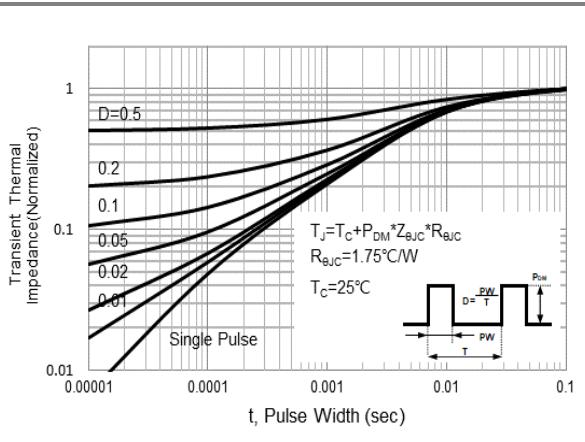


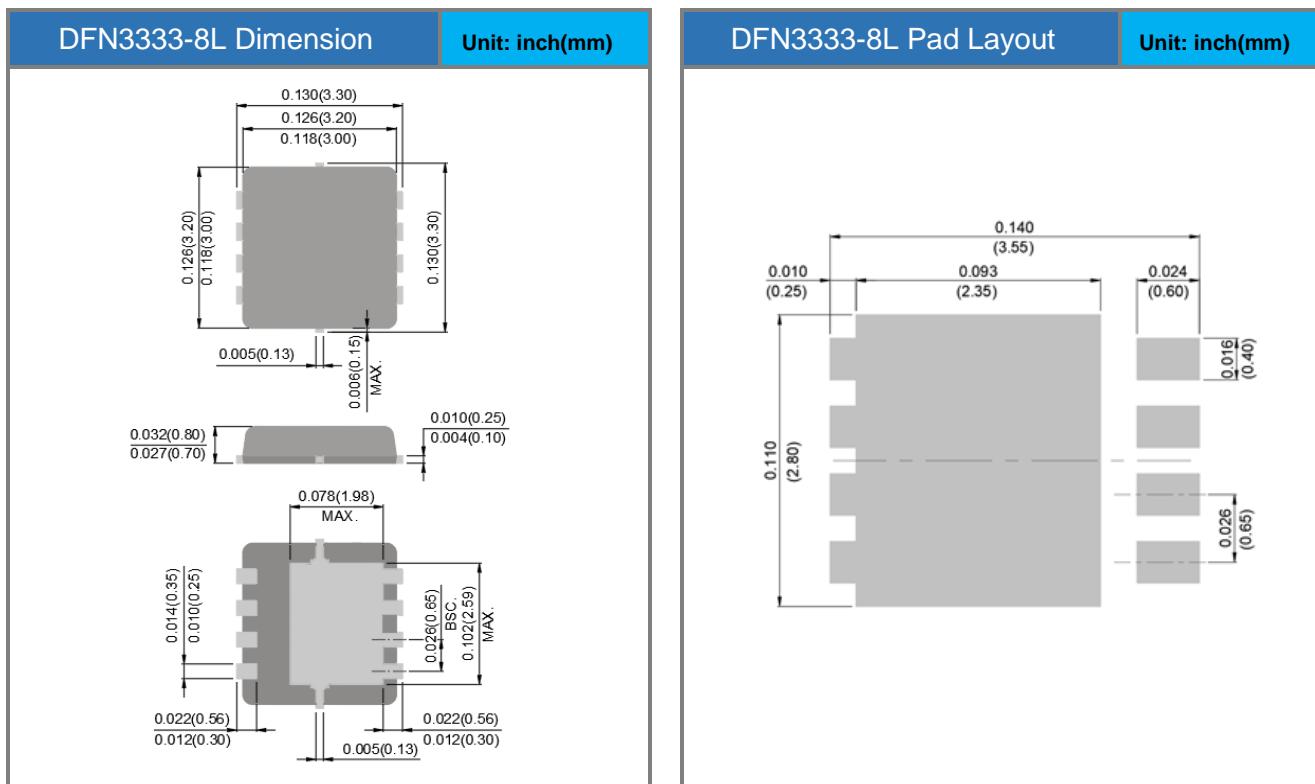
Fig.12 Normalized Transient Thermal Impedance

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Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJQ4542S6VP-AU	DFN3333-8L	5K pcs / 13" reel	542X

Packaging Information & Mounting Pad Layout



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